

CLAIMS

1. A method of manufacturing a semiconductor device comprising:

5 a first step of interposing an adhesive between a surface of a substrate on which an interconnect pattern is formed and a surface of a semiconductor chip on which electrodes are formed; and

10 a second step in which pressure is applied between said semiconductor chip and said substrate, said interconnect pattern and said electrodes are electrically connected, and said adhesive is caused to surround at least a part of a lateral surface of said semiconductor chip.

15 2. The method of manufacturing a semiconductor device as defined in claim 1,

20 wherein said adhesive is provided in the first step at a thickness greater than the interval between said semiconductor chip and said substrate after the second step, and is spread out beyond said semiconductor chip by applying pressure between said semiconductor chip and said substrate in the second step.

25 3 The method of manufacturing a semiconductor device as defined in claim 1,

wherein said adhesive is formed so as to substantially cover said lateral surface of said semiconductor chip.

4 The method of manufacturing a semiconductor device as defined in claim 1,

5 wherein said interconnect pattern and said electrodes are electrically connected by conductive particles dispersed in said adhesive.

5. The method of manufacturing a semiconductor device as defined in claim 1,

10 wherein before the first step, said adhesive is previously disposed on the surface of said semiconductor chip on which said electrodes are formed.

6. The method of manufacturing a semiconductor device as defined in claim 1,

15 wherein before the first step, said adhesive is previously disposed on the surface of said substrate on which said interconnect pattern is formed.

20 7. The method of manufacturing a semiconductor device as defined in claim 1,

wherein said adhesive includes a shading material.

Sub 8. A semiconductor device, comprising:  
25 a semiconductor chip having electrodes; a substrate having an interconnect pattern; and an adhesive; wherein said electrodes and said interconnect pattern are

electrically connected; and

wherein said adhesive is interposed between a surface of said substrate on which said interconnect pattern is formed and a surface of said semiconductor chip on which said electrodes  
5 are formed, so as to cover at least a part of a lateral surface of said semiconductor chip.

9. The semiconductor device as defined in claim 8,  
wherein said adhesive is formed so as to substantially  
10 cover said lateral surface of said semiconductor chip.

10. The semiconductor device as defined in claim 8,  
wherein conductive particles are dispersed in said  
adhesive to form an anisotropic conductive material.

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A1  
11. The semiconductor device as defined in claim 10,  
wherein said anisotropic conductive material is provided  
to cover the whole of said interconnect pattern.

20 12. The semiconductor device as defined in claim 11,  
wherein said adhesive includes a shading material.

sub 7  
A2  
25 13. A semiconductor device manufactured by the method as  
defined in any of claims 1 to 7.

14. A circuit board on which is mounted the semiconductor  
device as defined in any of claims 8 to 12.

Sub  
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Adp  
D<sub>4</sub> >